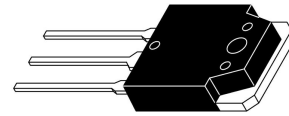


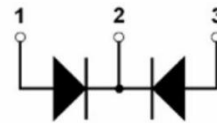
Features

- Low power loss,high efficiency
- High reliability
- RoHS product



Applications

- Snubber diode
- Switch power supply
- Anti parallel Diode for high frequency switching devices



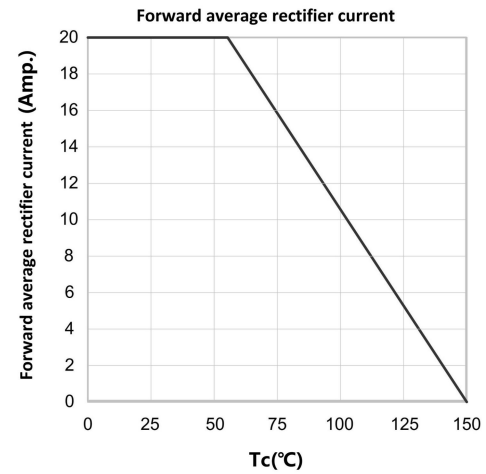
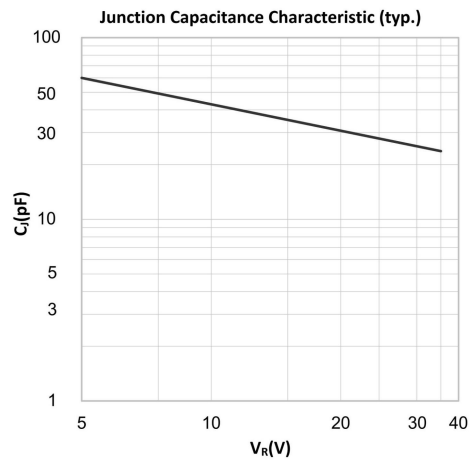
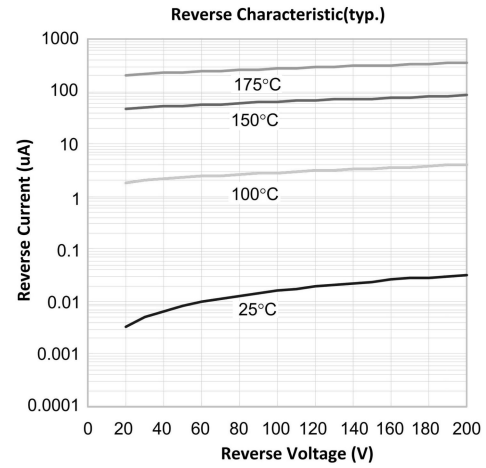
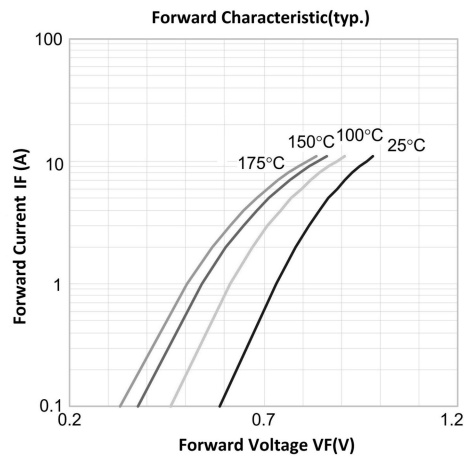
Absolute Maximum Ratings(Tc=25°C)

Parameter	Symbol	Test Conditions	Values	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		200	V
Average Output Current	I_o	duty=1/2, Tc=115°C Square wave	25*	A
Surge Current	I_{FSM}	Sine wave 10ms	250	A
Power Dissipation	P_D		156	W
Junction Temperature	T_J		-65~150	°C
Storage Temperature Range	T_{STG}		-65~150	
Thermal Resistance(3P)	$R_{\theta JC}$	Junction-to-Case	0.8	°C/W

Electrical Characteristics(Tc=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Reverse Current	I_{RRM}	$V_R=V_{RRM}$	Tj=25°C	-	-	50	μA
			Tj=125°C	-	-	500	μA
Forward Voltage Drop	V_{FM}	$I_{FM}=10.0A$	Tj=25°C	-	0.9	1.1	V
			Tj=125°C	-	-	1.0	V
Reverse Recovery Time	t_{rr}	IF=1A, VR=30V diF/dt=-200A/us	-	22	35	ns	

Electrical characteristics(Curves)



Package outline dimension

